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## FAIRCHILD

SEMICONDUCTOR®

November 2013

# **FQP13N50 N-Channel QFET® MOSFET**

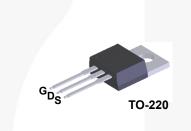
500 V, 12.5 A, 430 m  $\Omega$ 

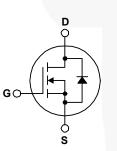
### Description

This N-Channel enhancement mode power MOSFET is • 12.5 A, 500 V,  $R_{DS(on)}$  = 430 m $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 45 nC) resistance, and to provide superior switching performance . Low Crss (Typ. 25 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

#### Features

- I<sub>D</sub> = 6.25 A





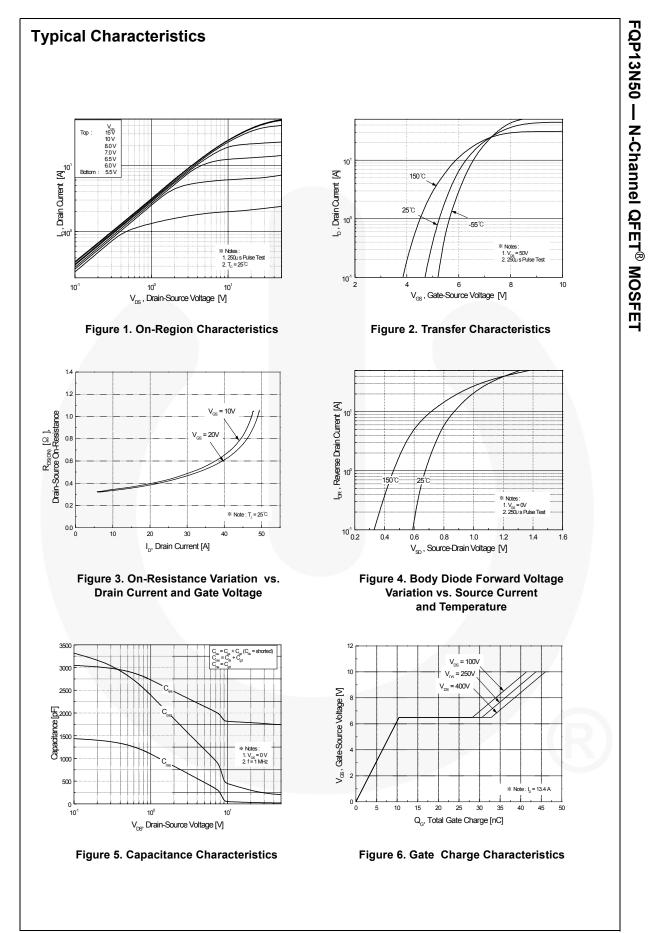
#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

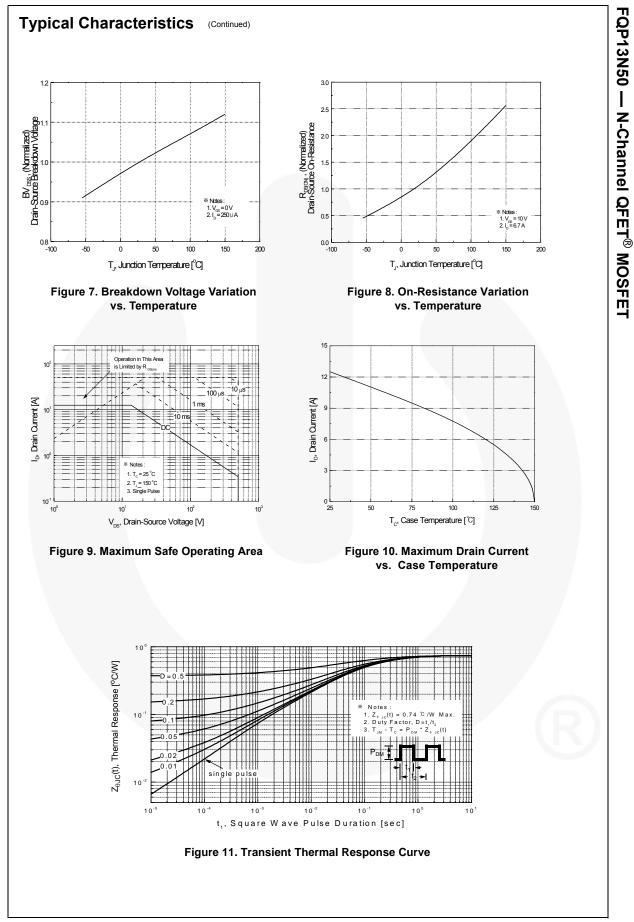
Symbol	Parameter		FQP13N50	Unit
V <sub>DSS</sub>	Drain-Source Voltage		500	V
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )		12.5	Α
	- Continuous (T <sub>C</sub> = 100°C)		7.9	A
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	50	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	810	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	12.5	A
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	17	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
PD	Power Dissipation ( $T_C = 25^{\circ}C$ )		170	W
	- Derate above 25°C		1.35	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
Τ <sub>L</sub>	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C

#### **Thermal Characteristics**

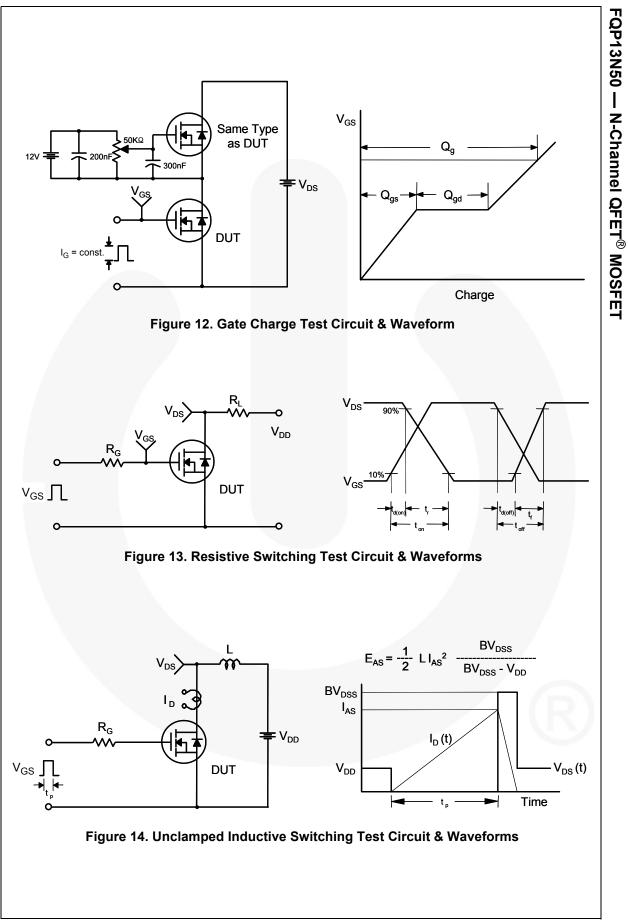
Symbol	Parameter	FQP13N50	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.74	°C/W
$R_{ hetaCS}$	Thermal Resistance, Case-to-Sink, Max.	0.5	°C/W

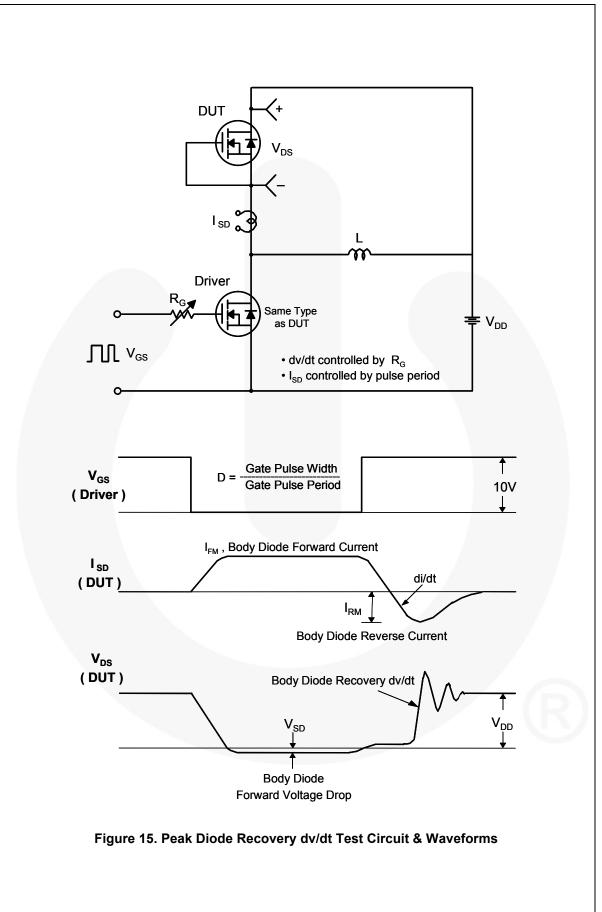
Symbol Off Cha BV <sub>DSS</sub>		FQP13N50	Packaç TO-22		ing Method Tube	Reel N/		Tape Width N/A		Quantity 50 units
Off Cha BV <sub>DSS</sub>	cal Char	racteristics	T <sub>C</sub> = 25°C ur	nless otherwise no	ed.					
Off Cha BV <sub>DSS</sub>	1	Parameter		Test C	onditions		Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>			I				1		1	
				/ _ <u>0 ) / I _ </u>	250 4					
		ce Breakdown Volt	0	/ <sub>GS</sub> = 0 V, I <sub>D</sub> =	250 μΑ		500			V
ΔΒV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient		ונ	$I_D$ = 250 $\mu$ A, Referenced to 25°C				0.48		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current		ont	$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 400 \text{ V}, T_{C} = 125^{\circ}\text{C}$					1 10	μA μA
I <sub>GSSF</sub>	Gate-Body	Leakage Current, I		/ <sub>GS</sub> = 30 V, V <sub>C</sub>	-				100	nA
		Leakage Current, I		/ <sub>GS</sub> = -30 V, V / <sub>GS</sub> = -30 V, V					-100	nA
IGSSR	Gale-Body	Leakage Current, I	Vevelse v	GS00 V, V	<u>)</u> S = 0 V				-100	IIA
On Cha	aracteristi	cs								
V <sub>GS(th)</sub>	Gate Thres	shold Voltage	V	/ <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> :	= 250 μA		3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain On-Resista		V	/ <sub>GS</sub> =10 V, I <sub>D</sub> =	6.25A			0.33	0.43	Ω
9 <sub>FS</sub>	Forward Tr	ansconductance	V	/ <sub>DS</sub> = 50 V, I <sub>D</sub>	= 6.25 A			10		S
Dynam	ic Charac	torictics						I	1	
C <sub>iss</sub>	Input Capa							1800	2300	pF
C <sub>oss</sub>	Output Capa			$V_{\rm DS} = 25  \rm V,  V_{\rm C}$	<sub>S</sub> = 0 V,			245	320	pr
C <sub>rss</sub>		ansfer Capacitance		= 1.0 MHz				245	35	pr
	ing Chara	atoristics							00	pi
<b>Switch</b> t <sub>d(on)</sub>	ing Chara Turn-On De	elay Time	v	/ <sub>DD</sub> = 250 V, I <sub>I</sub>	<sub>0</sub> = 13.4 A,			40	90	ns
<b>Switch</b> t <sub>d(on)</sub> t <sub>r</sub>	Turn-On De Turn-On Ri	elay Time ise Time		/ <sub>DD</sub> = 250 V, Ι <sub>[</sub> R <sub>G</sub> = 25 Ω	) = 13.4 A,			140	90 290	ns
Switch t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub>	Turn-On De Turn-On Ri Turn-Off De	elay Time ise Time elay Time				()		140 100	90 290 210	ns ns ns
Switch t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa	elay Time ise Time elay Time all Time	F	R <sub>G</sub> = 25 Ω		(Note 4)		140 100 85	90 290 210 180	ns ns ns ns
Switch $t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $Q_g$	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate	elay Time ise Time elay Time all Time Charge	F	R <sub>G</sub> = 25 Ω V <sub>DS</sub> = 400 V, I <sub>E</sub>		(Note 4)	  	140 100 85 45	90 290 210 180 60	ns ns ns ns nC
<b>Switch</b> t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub>	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate Gate-Source	elay Time ise Time elay Time all Time Charge ce Charge	F	R <sub>G</sub> = 25 Ω	) = 13.4 A,	· ·	  	140 100 85 45 11	90 290 210 180 60 	ns ns ns ns nC nC
Switch   t <sub>d(on)</sub> t <sub>r</sub> td(off)   t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate Gate-Sourc Gate-Drain	elay Time ise Time elay Time all Time Charge ce Charge o Charge	F	R <sub>G</sub> = 25 Ω / <sub>DS</sub> = 400 V, I <sub>C</sub> / <sub>GS</sub> = 10 V	) = 13.4 A,	(Note 4) (Note 4)	  	140 100 85 45	90 290 210 180 60	ns ns ns ns nC
Switch   t <sub>d(on)</sub> t <sub>r</sub> td(off)   t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate Gate-Source Gate-Drain	elay Time ise Time elay Time all Time Charge ce Charge	stics and	R <sub>G</sub> = 25 Ω / <sub>DS</sub> = 400 V, I <sub>C</sub> / <sub>GS</sub> = 10 V Maximum	9 = 13.4 A, Ratings	· ·	  	140 100 85 45 11	90 290 210 180 60 	ns ns ns ns nC nC
Switch $t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $Q_g$ $Q_{gs}$ $Q_{gd}$ Drain-S	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate Gate-Source Gate-Drain	elay Time ise Time elay Time all Time Charge ce Charge Charge Ode Characteri	stics and Source Diode	$R_{G} = 25 \Omega$ $V_{DS} = 400 V, I_{C}$ $V_{GS} = 10 V$ <b>Maximum</b> Forward Curr	9 = 13.4 A, Ratings	· ·	  	140 100 85 45 11 22	90 290 210 180 60  	ns ns ns nC nC nC
Switch $t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $Q_g$ $Q_{gs}$ $Q_{gd}$ Drain-S	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate Gate-Source Gate-Drain Source Dic Maximum F	elay Time ise Time elay Time all Time Charge ce Charge Charge <b>Ode Characteri</b> Continuous Drain-S	stics and Gource Diode ce Diode For	$R_{G} = 25 \Omega$ $V_{DS} = 400 V, I_{C}$ $V_{GS} = 10 V$ <b>Maximum</b> Forward Curr	p = 13.4 A, Ratings ent	<u> </u>	    	140 100 85 45 11 22	90 290 210 180 60   12.5	ns ns ns nC nC nC A
Switch   t <sub>d(on)</sub> t <sub>r</sub> t_d(off)   t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub> Drain-S   I <sub>SM</sub>	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate Gate-Source Gate-Drain Source Dic Maximum ( Maximum F Drain-Source	elay Time ise Time elay Time all Time Charge ce Charge c Charge <b>Ode Characteri</b> Continuous Drain-S Pulsed Drain-Sourc	stics and Source Diode Diode Forn Voltage V	$R_{G} = 25 \Omega$ $V_{DS} = 400 V, I_{C}$ $V_{GS} = 10 V$ <b>Maximum</b> Forward Current	ent 12.5 A	<u> </u>	      	140 100 85 45 11 22	90 290 210 180 60   12.5 50	ns ns ns nC nC nC A A

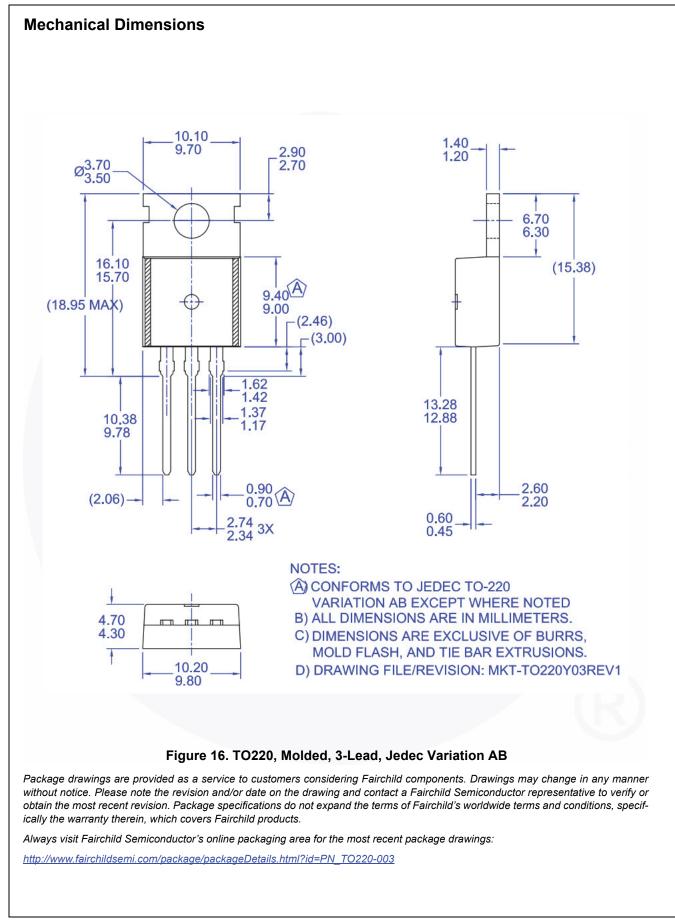




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FQP13N50 — N-Channel QFET<sup>®</sup> MOSFET



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Preliminary

No Identification Needed

Obsolete

First Production

**Full Production** 

Not In Production

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